NP05-11462-1E

32 Mbit Mobile FCRAM™
1.8 V, Burst Mode & Page Mode
MB82DBS02163F-70L

■ FEATURES

- ・Pseudo SRAM with Asynchronous / Synchronous SRAM Interface
- ・COSMORAM (Common Specifications for Mobile RAM) Revision 2
- ・Burst Mode Function (Synchronous Operation)
- ・8 Words Page Read Access Capability
- ・Byte Control by $\overline{\text{LB}}$, $\overline{\text{UB}}$
- ・Low Power Consumption
- ・Various Power Down Mode
    - Sleep
    - 4 Mbit Partial
    - 8 Mbit Partial
- ・Shipping Form: Chip / Wafer, 71-pin FBGA Package

■ MAIN SPECIFICATIONS

Part Number		MB82DBS02163F-70L
Organization		2 M Word × 16 bit
Supply Voltage		1.7 V to 1.95 V
Burst Frequency (Max.)	RL＝6	83 MHz
CLK Access Time (Max.)	RL＝5, 6	8 ns
Page Address Access Time (Max.)		20 ns
Address Access Time (Max.)		70 ns
Active Current (Max.)		30 mA
Standby Current (Max.)		120 μA
Power Down Current (Max.)	Sleep	10 μA

Note: FCRAM is a trademark of Fujitsu Microelectronics Limited, Japan.

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